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Contents

v	<i>Authors</i>
vii	<i>Conference Committee</i>

0D STRUCTURES AND CLUSTERS I

11085 07	Engineering site-controlled quantum dots for optical quantum information processing (Invited Paper) [11085-6]
----------	--

0D STRUCTURES AND CLUSTERS II

11085 0F	Red emission carbon dots for microLED application [11085-14]
11085 0H	Preparation of highly stability $Zn_xCd_{1-x}S$ white light quantum dots by silica coating [11085-16]

LOW-D DEVICES

11085 0L	Opportunities for transition metal oxide devices in solid state random number generators (Invited Paper) [11085-20]
----------	--

2D AND LAYERED STRUCTURES I

11085 0Q	Effect of annealing on electrochemical stability of chemically preintercalated bilayered vanadium oxide cathodes in batteries [11085-25]
----------	---

2D AND LAYERED STRUCTURES II

11085 0R	Two-dimensional hybrid organic-inorganic semiconductors deposited by resonant infrared, matrix-assisted pulsed laser evaporation (Invited Paper) [11085-26]
11085 0T	Near-infrared photonic phase-change properties of transition metal ditellurides (Invited Paper) [11085-28]
11085 0U	The effect of growth temperature and metal-to-chalcogen on the growth of WSe_2 by molecular beam epitaxy (Invited Paper) [11085-29]

2D AND LAYERED STRUCTURES III

- 11085 0W **Electric field induced variations of excited state lifetimes and photoluminescence spectra in 2D heterostructures** [11085-31]
- 11085 0Y **Revealing of intrinsic intralayer phonon coupling by polarization-resolved analysis in monolayer MoS₂** [11085-33]

POSTER SESSION

- 11085 12 **Microstructural characterization and phase transitions in polycrystalline and nanocrystalline doped zirconia for incorporation in medical prosthesis** [11085-36]
- 11085 13 **Study of magnetic properties of a nano-graphene monolayer within Ising ferromagnetic model with mixed spins** [11085-37]
- 11085 15 **Polarization-dependent optical absorption in phosphorene flakes** [11085-39]
- 11085 16 **Improved carrier confinement and strain profile in heterogeneously coupled SK-SML quantum dot heterostructure** [11085-40]
- 11085 17 **Investigation of various capping layer configuration on heterogeneously coupled SML on SK quantum dots heterostructure** [11085-41]
- 11085 18 **The effects of V-III ratio on structural and optical properties of self-assembled InAs quantum dots** [11085-42]
- 11085 19 **The effect of growth rate variation on structural and optical properties of self assembled InAs quantum dots** [11085-43]
- 11085 1A **A detailed investigation on the impact of variation in monolayer coverage on optical properties of InAs/GaAs multilayer quantum dot heterostructure** [11085-44]
- 11085 1D **Effect of substrate temperature variation on the structural and optical properties of self assembled InAs quantum dots** [11085-47]
- 11085 1F **Realizing Li-ion full cell using LiFePO₄ cathode and Mn₃O₄-mesoporous carbon composite anode for energy storage applications** [11085-49]
- 11085 1J **HCDI performance of Na-2x3 and Na-2x4 nanowires for water desalination** [11085-53]
- 11085 1K **Influence of quaternary (In_{0.21}Al_{0.21}Ga_{0.58}As) capping on the performance of InAs quantum dot infrared photodetector** [11085-54]
- 11085 1N **Optical and structural investigation of ex-situ passivated strain coupled InAs surface quantum dots** [11085-57]
- 11085 1O **The enhancement in luminescence property of chemically passivated near surface quantum well and quantum dots** [11085-58]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

A., Abhilash, 1F
Aanand, Abhijeet, 18, 19, 1D
Agarwal, Anubhav, 18, 19
Andris, Ryan, 0Q, 1J
Angelsky, O. V., 13
Avelino, Wellington, 0L
Balachandran, Prasanna V., 0U
Bogdanowicz, R., 15
Bruma, Alina, 12
Chakrabarti, Subhananda, 16, 17, 18, 19, 1A, 1D, 1K, 1N, 1O
Cheng, Li-Jing, 0F
Chung, Shu-Ru, 0H
Clites, Mallory, 0Q
Constantin, Costel, 0U
Craus, Mihai-Liviu, 12
Dahale, Rishabh A., 18, 19
Das, Debabrata, 17, 18, 19, 1A, 1D, 1K, 1N, 1O
Davydov, Albert, 0T
Dongre, Suryansh, 18, 19, 1A, 1D
Doroshkevych, Oleksandr S., 12
Engel, Michael, 0W
Fonseca, Leonardo, 0L
Gazi, Sanowar Alam, 18, 19, 1A, 1D
Gocalinska, A., 07
Huang, Teng-De, 0Y
Huang, Yun-Xuan, 0H
Ivashko, V. V., 13
Jakóbczyk, P., 15
Jaramillo, R., 0T
Jayalekshmi, S., 1F
Juska, G., 07
K. M., Anilkumar, 1F
Konstantinova, Tatiana E., 12
Krylyuk, Sergiy, 0T
Kumar, Ravinder, 1K
Lan, Yann-Wen, 0Y
Li, Yifei, 0T
Litwin, Peter M., 0U
Liu, Ye, 0F
Lu, Ting-Hua, 0Y
M., Manoj, 1F
Maksimyak, P. P., 13
Mantri, Manas Ranjan, 1N, 1O
Marques, Bernardo L., 0L
McDonnell, Stephen, 0U
Medeiros-Ribeiro, Gilberto, 0L
Mondal, Shubham, 18, 19, 1N, 1O
Moroni, S. T., 07
Nilsson, Victoria, 0U
Novy, Frantisek, 12
Ohlberg, Douglas A. A., 0L
Panda, Debiprasad, 17, 18, 19, 1A, 1D, 1K, 1N, 1O
Pansare, Amol V., 1N, 1O
Patel, Aditya, 1A
Paul, Sritoma, 18, 19, 1N, 1O
Pelucchi, E., 07
Pomerantseva, Ekaterina, 0Q, 1J
Ramavath, Rajkumar, 16, 17
Ranjbar, I., 07
Raut, Pravin, 16, 17
Ridley, Phillip, 0Q, 1J
Saha, Jhuma, 16, 17, 1K
Sales, Maria Gabriela, 0U
Savin, Adriana, 12
Simbulan, Kristan Bryan, 0Y
Singh, Akshay, 0T
Steiner, Mathias, 0W
Stiff-Roberts, Adrienne D., 0R
Tanyi, Ekembu K, 0F
Tongbram, Binita, 1K
Turchenko, Vitalii, 12
Varo, S., 07
Wang, Yi-Chieh, 0F
Wieloszyńska, A., 15
Wright, Niara E., 0R
Wu, Bo, 0F

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Session Chairs

- 1 1D Structures
Nobuhiko P. Kobayashi, University of California, Santa Cruz
(United States)
- 2 0D Structures and Clusters I
Rachel S. Goldman, University of Michigan (United States)
- 3 ALD and PVD
Albert V. Davydov, National Institute of Standards and Technology
(United States)
- 4 0D Structures and Clusters II
Alina Bruma, University of Maryland, College Park (United States)
- 5 Low-D Devices
Rafael Jaramillo, Massachusetts Institute of Technology
(United States)
- 6 2D and Layered Structures I
Babak Nikoobakht, National Institute of Science and Technology
(United States)
- 7 2D and Layered Structures II
Sonia Conesa-Boj, Technische Universiteit Delft (Netherlands)
- 8 2D and Layered Structures III
George T. Wang, Sandia National Laboratories (United States)